

## ABSTRACT OF THE DISCLOSURE

A method of reclaiming silicon wafers including a film removal process, a polishing process, and a cleaning process, wherein a heating / removal process for removing a silicon wafer surface part by heating at 150 - 300°C for 20 minutes to 5 hours is further included between the film removal process and the polishing process is provided. The present invention provides a useful method of reclaiming silicon wafers that removes Cu not only deposited on a surface but also penetrated inside of a silicon wafer, and does not give Cu contamination inside of the silicon wafer.